2SC2732

Silicon NPN Epitaxial

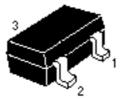
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Application

UHF frequency converter

Outline

MPAK



- 1. Emitter
- 2 Rase
- 3. Collector



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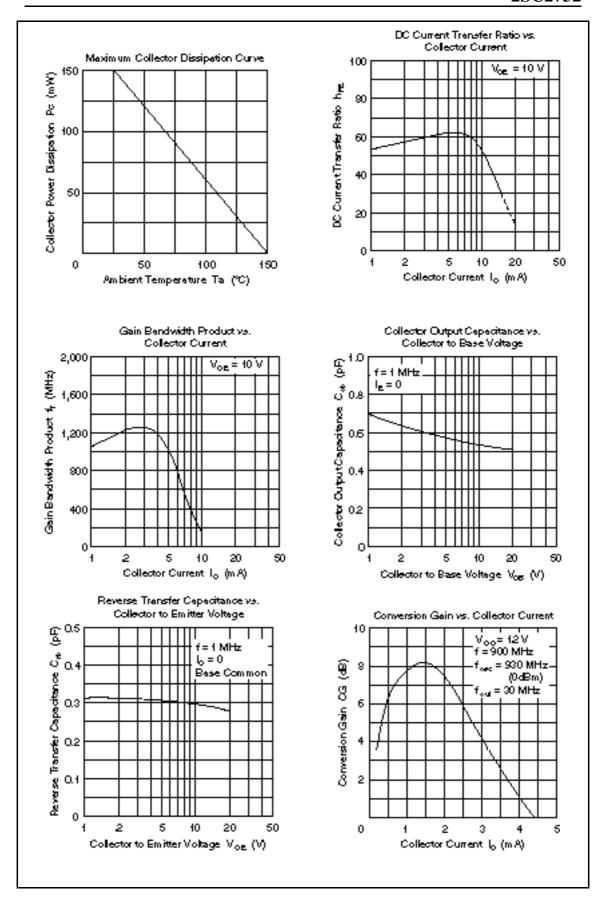
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V _{CEO}	25	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I _c	20	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

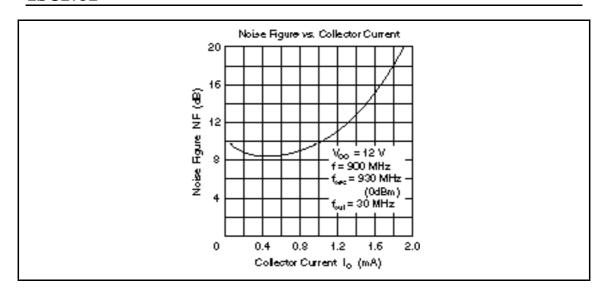
Electrical Characteristics ($Ta = 25^{\circ}C$)

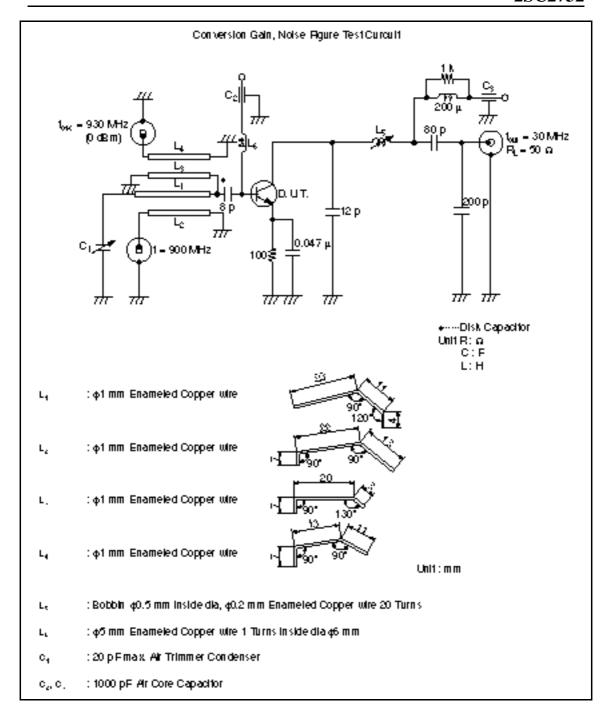
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	25	_	_	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 10 \text{ V}, I_{C} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	5	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
DC current transfer ratio	h _{FE}	30	60	_		V_{CE} = 10 V, I_{C} = 3 mA
Gain bandwidth product	f _T	700	1000	_	MHz	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$
Collector output capacitance	Cob	_	0.5	0.8	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Conversion gain	CG	_	7.0	_	dB	$V_{CC} = 12 \text{ V}, I_{C} = 1 \text{ mA},$ f = 900 MHz, $f_{OSC} = 930 \text{ MHz (0dBm)},$ $f_{out} = 30 \text{ MHz}$
Noise figure	NF	_	10.0	_	dB	$V_{CC} = 12 \text{ V}, I_{C} = 1 \text{ mA},$ f = 900 MHz, $f_{OSC} = 930 \text{ MHz (0dBm)},$ $f_{out} = 30 \text{ MHz}$

Note: Marking is "EC".



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